Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-009-2231

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Inclosure Material:	
Metal	
Overall Length:	
1.453 inches	
Overall Diameter:	
0.667 inches	
Mounting Facility Qua	ntity:
1	
Electrode Internally-el	ectrically Connected To Case:
Anode	
Mounting Method:	
Threaded stud	
<b>Overall Width Across</b>	Flats:
Between 0.667 inches a	and 0.687 inches
Thread Size:	
0.250 inches	
Semiconductor Materi	al:
Silicon	
Voltage Rating In Volt	s Per Characteristic:
5.6 regulator voltage	
Voltage Tolerance In F	Percent:
-5.0/+5.0	
Current Rating Per Ch	aracteristic:
8.50 amperes source ci	utoff current horsepower metric
Power Rating Per Cha	racteristic:
50.0 watts small-signal	input power, common-collector preset
Maximum Operating T	empurature Per Measurement Point:
150.0 degrees celsius c	ase
Test Data Document:	
81349-mil-s-19500 spe	cification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes comm	nercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and perfe	ormance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designation	ator:
Unf	
Terminal Type And Qu	iantity:
1 threaded stud and 1 ta	ab, solder lug
Specification Data:	
81349-mil-s-19500/358	government specification
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	

## NSN 5961-01-009-2231

Diode Semiconductor Device - Page 2 of 2

**Fiig:** A110a0

